

isc Silicon NPN Power Transistor

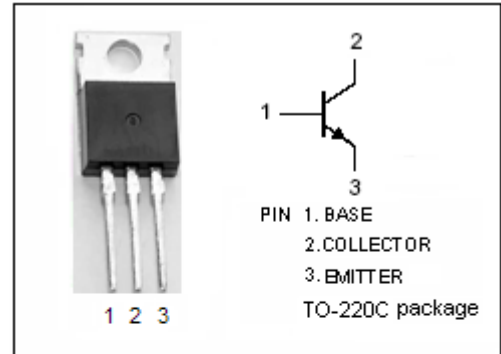
2SC2929

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 400V(\text{Min})$
- High Switching Speed
- High Reliability

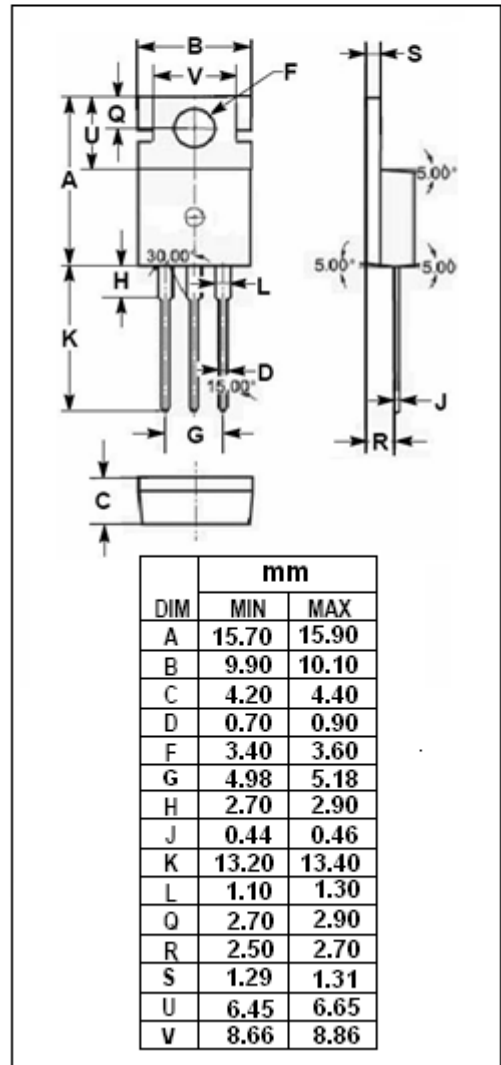
APPLICATIONS

- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	450	V
V_{CEO}	Collector-Emitter Voltage	400	V
$V_{CEO(SUS)}$	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base voltage	7	V
I_C	Collector Current-Continuous	3	A
I_B	Base Current-Continuous	1	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	40	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-45~150	$^\circ\text{C}$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	3.0	$^\circ\text{C/W}$

isc Silicon NPN Power Transistor

2SC2929

ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=10\text{mA}; I_B=0$	400			V
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=0.5\text{A}; I_B=0$	400			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=0.1\text{mA}; I_E=0$	450			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=0.1\text{mA}; I_C=0$	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.2\text{A}$			0.3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=1\text{A}; I_B=0.2\text{A}$			0.9	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=450\text{V}; I_E=0$			0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=7\text{V}; I_C=0$			0.1	mA
h_{FE}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=5\text{V}$	20		50	

Switching times

t_{on}	Turn-on Time	$I_C=3\text{A}, I_{B1}=-I_{B2}=0.6\text{A}$ $R_L=20\Omega; P_W=20\mu\text{s}$ Duty Cycle $\leq 2\%$			1.5	μs
t_{stg}	Storage Time				2.0	μs
t_f	Fall Time				0.8	μs